

N-channel TrenchMOS logic level FET 13 March 2014

Product data sheet

### 1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 3. Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

### 4. Quick reference data

| Table 1. C        | Quick reference data    |  |     |     |     |      |
|-------------------|-------------------------|--|-----|-----|-----|------|
| Symbol            | Parameter               | Conditions   | Min | Тур | Max | Unit |
| V <sub>DS</sub>   | drain-source voltage    | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C  | -   | -   | 100 | V    |
| I <sub>D</sub>    | drain current           | V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>                        | -   | -   | 39  | А    |
| P <sub>tot</sub>  | total power dissipation | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>   | -   | -   | 158 | W    |
| Static char       | acteristics             | · · · · ·  | , I |     |     |      |
| R <sub>DSon</sub> | drain-source on-state   | $V_{GS}$ = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C                                      | -   | -   | 43  | mΩ   |
|                   | resistance              | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C                                | -   | 29  | 39  | mΩ   |
|                   |                         | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C;<br>Fig. 11; Fig. 12            | -   | 34  | 40  | mΩ   |
| Dynamic cl        | haracteristics          | · · · ·  | ľ   |     |     |      |
| Q <sub>GD</sub>   | gate-drain charge       | $V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 80 \text{ V};$<br>$T_j = 25 \text{ °C}; Fig. 13$ | -   | 20  | -   | nC   |

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| Symbol               | Parameter   | Conditions  |  | Min | Тур | Мах | Unit |
|----------------------|---|---|--|-----|-----|-----|------|
| Avalanche ruggedness |   |   |  |     |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-<br>source avalanche<br>energy | $I_D$ = 39 A; $V_{sup}$ ≤ 100 V; $R_{GS}$ = 50 Ω;<br>$V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped |  | -   | -   | 182 | mJ   |

#### **Pinning information** 5.

| Table 2. | Pinning | information                       |                    |                |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin      | Symbol  | Description                       | Simplified outline | Graphic symbol |
| 1        | G       | gate                              | mb                 | D              |
| 2        | D       | drain[1]                          |                    |                |
| 3        | S       | source                            |                    | G-UFA          |
| mb       | D       | mounting base; connected to drain | D2PAK (SOT404)     | mbb076 S       |

[1] It is not possible to make a connection to pin 2.

#### **Ordering information** 6.

#### Table 3. **Ordering information** Type number Package Name Description Version BUK9640-100A D2PAK plastic single-ended surface-mounted package (D2PAK); 3 leads SOT404 (one lead cropped)

#### Marking 7.

| Table 4. Marking codes |              |
|------------------------|--------------|
| Type number            | Marking code |
| BUK9640-100A           | BUK9640-100A |

#### **Limiting values** 8.

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol   | Parameter            | Conditions                                      |  | Min | Max | Unit |
|--|----------------------|---|--|-----|-----|------|
| V <sub>DS</sub>  | drain-source voltage | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C |  | -   | 100 | V    |
| V <sub>DGR</sub>   | drain-gate voltage   | R <sub>GS</sub> = 20 kΩ                         |  | -   | 100 | V    |
| V <sub>GS</sub>  | gate-source voltage  |   |  | -15 | 15  | V    |
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| Symbol               | Parameter                                    | Conditions   | Min | Мах | Unit |
|----------------------|--|--|-----|-----|------|
| P <sub>tot</sub>     | total power dissipation                      | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>   | -   | 158 | W    |
| I <sub>D</sub>       | drain current                                | T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2; Fig. 3</u>  | -   | 39  | А    |
|                      |  | T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>   | -   | 28  | А    |
| I <sub>DM</sub>      | peak drain current                           | $T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3   | -   | 159 | А    |
| T <sub>stg</sub>     | storage temperature                          |  | -55 | 175 | °C   |
| Tj                   | junction temperature                         |  | -55 | 175 | °C   |
| Source-dra           | in diode                                     |  | I   |     |      |
| I <sub>S</sub>       | source current                               | T <sub>mb</sub> = 25 °C  | -   | 39  | А    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^\circ C$  | -   | 159 | А    |
| Avalanche            | ruggedness                                   |  | 1   |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $    I_D = 39 \text{ A}; V_{sup} \le 100 \text{ V}; \text{ R}_{GS} = 50 \Omega;                                  $ | -   | 182 | mJ   |

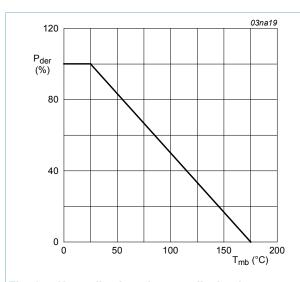


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

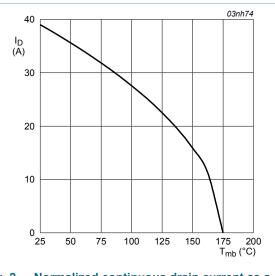
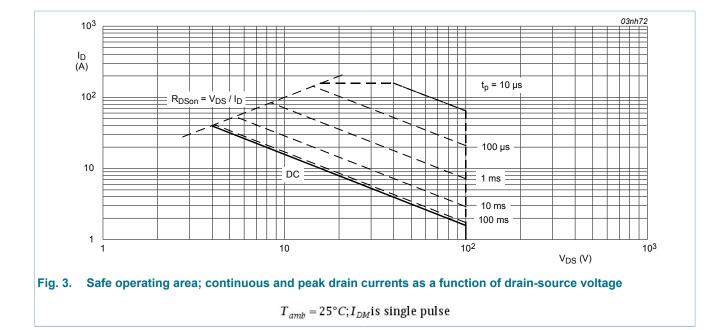


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

 $T_{amb} = 25^{\circ}C; I_{DM}$  is single pulse

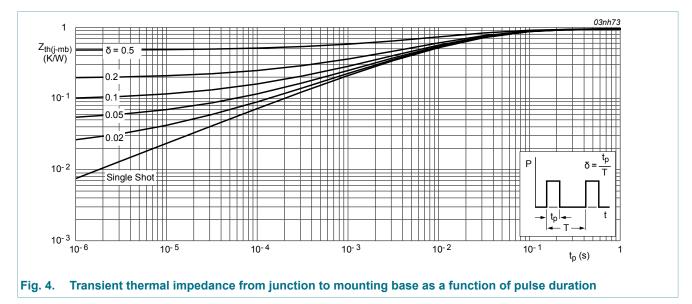
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### 9. Thermal characteristics

| Table 6. Thermal characteristics |   |  |  |     |     |      |      |
|----------------------------------|---|--|--|-----|-----|------|------|
| Symbol                           | Parameter   | Conditions   |  | Min | Тур | Мах  | Unit |
| R <sub>th(j-mb)</sub>            | thermal resistance<br>from junction to<br>mounting base | Fig. <u>4</u>  |  | -   | -   | 0.95 | K/W  |
| R <sub>th(j-a)</sub>             | thermal resistance<br>from junction to<br>ambient       | mounted on a printed-circuit board;<br>minimum footprint |  | -   | 50  | -    | K/W  |



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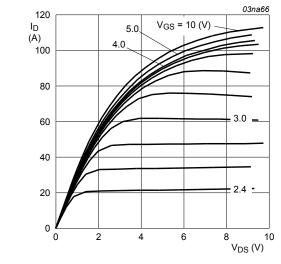
## **10. Characteristics**

| Symbol               | Parameter                           | Conditions   | Min | Тур  | Мах  | Unit |
|----------------------|-------------------------------------|--|-----|------|------|------|
| Static chara         | acteristics                         | · · · · ·  |     |      |      |      |
| V <sub>(BR)DSS</sub> | drain-source                        | $I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C   | 100 | -    | -    | V    |
|                      | breakdown voltage                   | $I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C  | 89  | -    | -    | V    |
| V <sub>GS(th)</sub>  | gate-source threshold voltage       | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C;<br>Fig. 10                                  | 1   | 1.5  | 2    | V    |
|                      |                                     | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C;<br>Fig. 10 | 0.5 | -    | -    | V    |
|                      |                                     | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$<br>Fig. 10                        | -   | -    | 2.3  | V    |
| I <sub>DSS</sub>     | drain leakage current               | V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C                        | -   | -    | 500  | μA   |
|                      |                                     | $V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C  | -   | 0.05 | 10   | μA   |
| I <sub>GSS</sub>     | gate leakage current                | V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                          | -   | 2    | 100  | nA   |
|                      |                                     | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                         | -   | 2    | 100  | nA   |
| R <sub>DSon</sub>    | drain-source on-state<br>resistance | $V_{GS}$ = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C                                | -   | -    | 43   | mΩ   |
| resi                 |                                     | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C;<br>Fig. 11; Fig. 12     | -   | -    | 100  | mΩ   |
|                      |                                     | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C                          | -   | 29   | 39   | mΩ   |
|                      |                                     | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C;<br>Fig. 11; Fig. 12      | -   | 34   | 40   | mΩ   |
| Dynamic ch           | naracteristics                      | · · · · · ·  | '   |      |      |      |
| Q <sub>G(tot)</sub>  | total gate charge                   | $I_D$ = 25 A; $V_{DS}$ = 80 V; $V_{GS}$ = 5 V;   | -   | 48   | -    | nC   |
| Q <sub>GS</sub>      | gate-source charge                  | T <sub>j</sub> = 25 °C; <u>Fig. 13</u>   | -   | 5.4  | -    | nC   |
| Q <sub>GD</sub>      | gate-drain charge                   |  | -   | 20   | -    | nC   |
| C <sub>iss</sub>     | input capacitance                   | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;                                      | -   | 2304 | 3072 | pF   |
| C <sub>oss</sub>     | output capacitance                  | T <sub>j</sub> = 25 °C; <u>Fig. 14</u>   | -   | 222  | 266  | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance        |  | -   | 151  | 207  | pF   |
| t <sub>d(on)</sub>   | turn-on delay time                  | $V_{DS}$ = 30 V; R <sub>L</sub> = 1.2 $\Omega$ ; V <sub>GS</sub> = 5 V;                        | -   | 20   | -    | ns   |
| t <sub>r</sub>       | rise time                           | R <sub>G(ext)</sub> = 10 Ω; T <sub>j</sub> = 25 °C   | -   | 135  | -    | ns   |
| t <sub>d(off)</sub>  | turn-off delay time                 |  | -   | 125  | -    | ns   |
| t <sub>f</sub>       | fall time                           |  | -   | 90   | -    | ns   |
| L <sub>D</sub>       | internal drain inductance           | from upper edge of drain mounting base to centre of die; $T_i = 25 \degree C$                  | -   | 2.5  | -    | nH   |

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| Symbol          | Parameter                  | Conditions  | Min | Тур  | Max | Unit |
|-----------------|----------------------------|---|-----|------|-----|------|
|                 |                            | from drain lead 6 mm from package to centre of die; $T_j$ = 25 °C       | -   | 4.5  | -   | nH   |
| L <sub>S</sub>  | internal source inductance | from source lead to source bond pad; $T_j = 25 \ ^{\circ}C$             | -   | 7.5  | -   | nH   |
| Source-drai     | in diode                   |   |     |      |     |      |
| V <sub>SD</sub> | source-drain voltage       | $I_{S}$ = 25 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 15</u>         | -   | 0.85 | 1.2 | V    |
| t <sub>rr</sub> | reverse recovery time      | I <sub>S</sub> = 37 A; dI <sub>S</sub> /dt = -100 A/μs;                 | -   | 60   | -   | ns   |
| Qr              | recovered charge           | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C | -   | 240  | -   | nC   |





 $T_j=25^\circ C; t_p=300 \mu s$ 

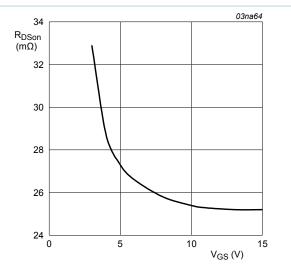
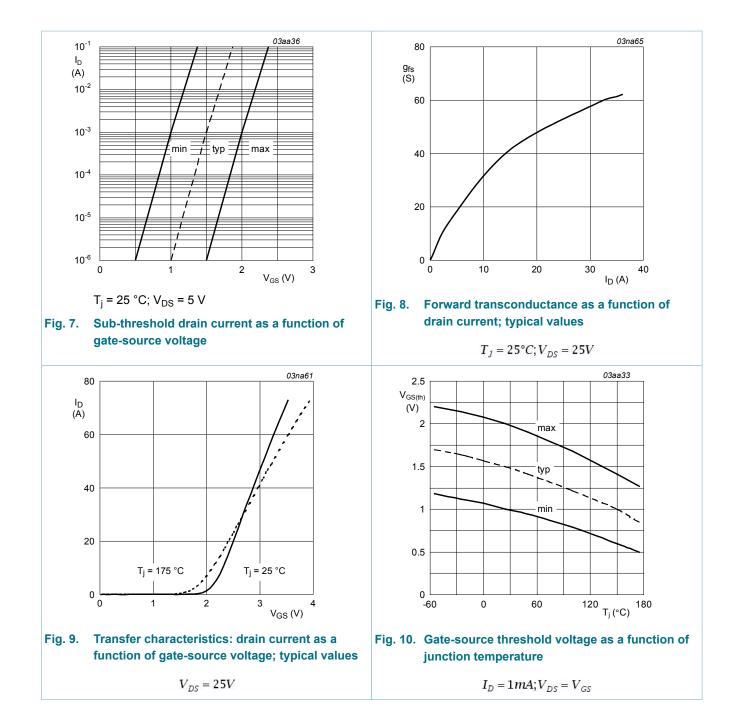


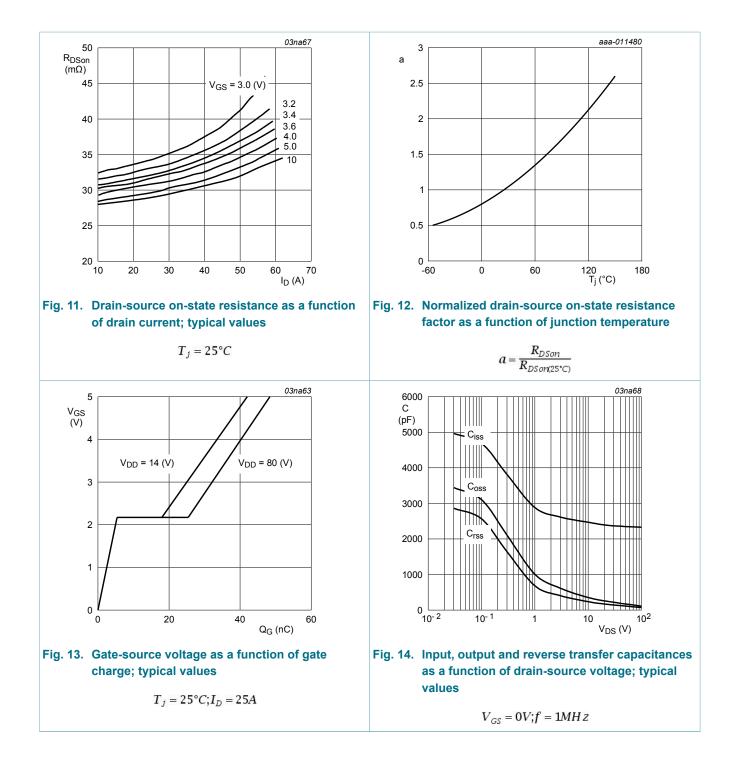
Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

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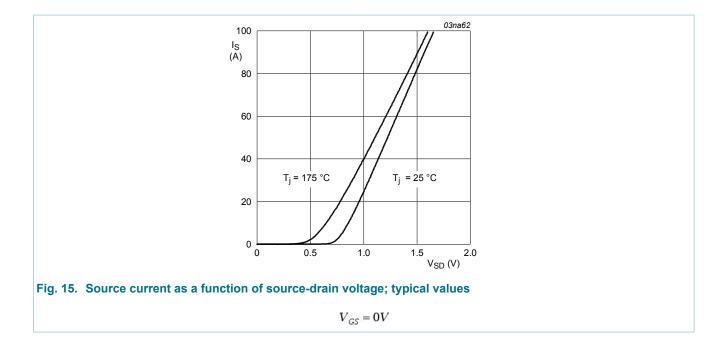
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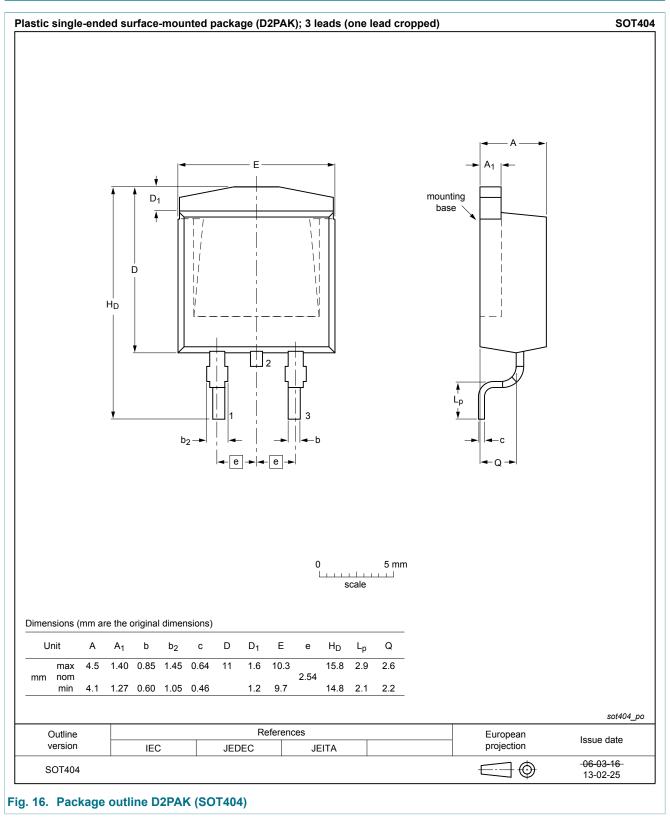
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### 11. Package outline



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### 12. Legal information

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| Document status [1][2]               | Product<br>status [ <u>3]</u> | Definition  |
|--------------------------------------|-------------------------------|---|
| Objective<br>[short] data<br>sheet   | Development                   | This document contains data from<br>the objective specification for product<br>development. |
| Preliminary<br>[short] data<br>sheet | Qualification                 | This document contains data from the preliminary specification.                             |
| Product<br>[short] data<br>sheet     | Production                    | This document contains the product specification.   |

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